Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

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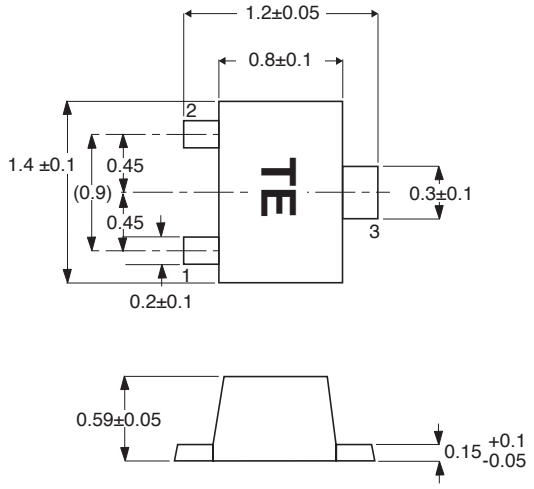
NEC's NPN SILICON TRANSISTOR | NE681M03

FEATURES

- **NEW M03 PACKAGE:**
  - Smallest transistor outline package available
  - Low profile/0.59 mm package height
  - Flat lead style for better RF performance
- **HIGH GAIN BANDWIDTH PRODUCT:**
  f_T = 7 GHz
- **LOW NOISE FIGURE:**
  NF = 1.4 dB

OUTLINE DIMENSIONS (Units in mm)

PACKAGE OUTLINE M03



PIN CONNECTIONS
1. Emitter
2. Base
3. Collector

DESCRIPTION

NEC's NE681M03 transistor is ideal for low noise, high gain, and low cost amplifier applications. NEC's new low profile/ flat lead style "M03" package is ideal for today's portable wireless applications. The NE681 is also available in chip, Micro-x, and six different low cost plastic surface mount package styles.

ELECTRICAL CHARACTERISTICS (T_A = 25°C)

PART NUMBER EIAJ[1] REGISTERED NUMBER PACKAGE OUTLINE		NE681M03 2SC5433 M03			
SYMBOLS	**PARAMETERS AND CONDITIONS**	**UNITS**	**MIN**	**TYP**	**MAX**
f_T	Gain Bandwidth at V_{CE} = 3 V, I_C = 7 mA, f = 1 GHz	GHz	4.5	7.0	
NF	Noise Figure at V_{CE} = 3 V, I_C = 7 mA, f = 1 GHz	dB		1.4	2.7
$\|S_{21E}\|^2$	Insertion Power Gain at V_{CE} = 3 V, I_C = 7 mA, f = 1 GHz	dB	10	12	
h_{FE}[2]	Forward Current Gain at V_{CE} = 3 V, I_C = 7 mA		80		145
I_{CBO}	Collector Cutoff Current at V_{CB} = 10 V, I_E = 0	μA			0.8
I_{EBO}	Emitter Cutoff Current at V_{EB} = 1 V, I_C = 0	μA			0.8
C_{RE}[3]	Feedback Capacitance at V_{CB} = 3 V, I_E = 0, f = 1 MHz	pF			0.9

Notes:
1. Electronic Industrial Association of Japan.
2. Pulsed measurement, pulse width ≤ 350 μs, duty cycle ≤ 2 %.
3. Capacitance is measured with emitter and case connected to the guard terminal at the bridge.

ABSOLUTE MAXIMUM RATINGS[1] (T_A = 25°C)

SYMBOLS	PARAMETERS	UNITS	RATINGS
V_{CBO}	Collector to Base Voltage	V	20
V_{CEO}	Collector to Emitter Voltage	V	10
V_{EBO}	Emitter to Base Voltage	V	1.5
I_C	Collector Current	mA	65
P_T	Total Power Dissipation	mW	125
T_J	Junction Temperature	°C	150
T_{STG}	Storage Temperature	°C	-65 to +150

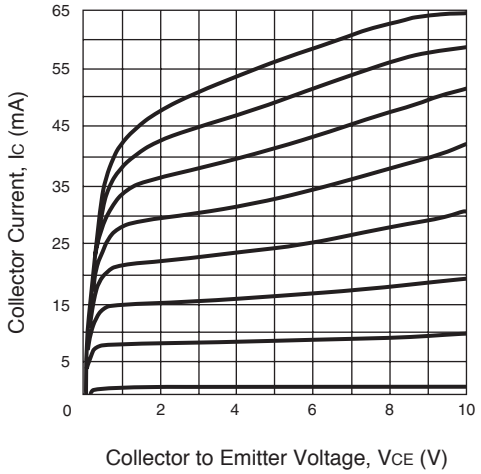
Note:
1. Operation in excess of any one of these parameters may result in permanent damage.

ORDERING INFORMATION

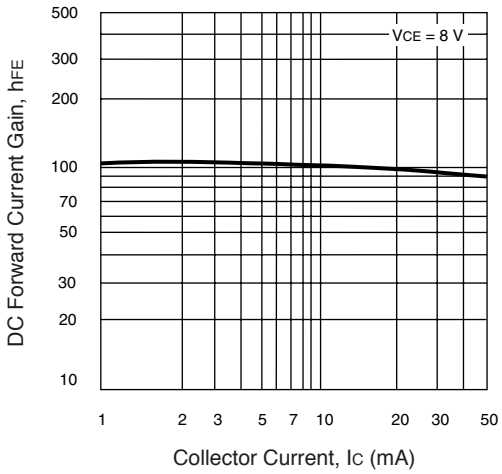
PART NUMBER	QUANTITY
NE681M03-A	
NE681M03-T1-A	

TYPICAL PERFORMANCE CURVES (T_A = 25°C)

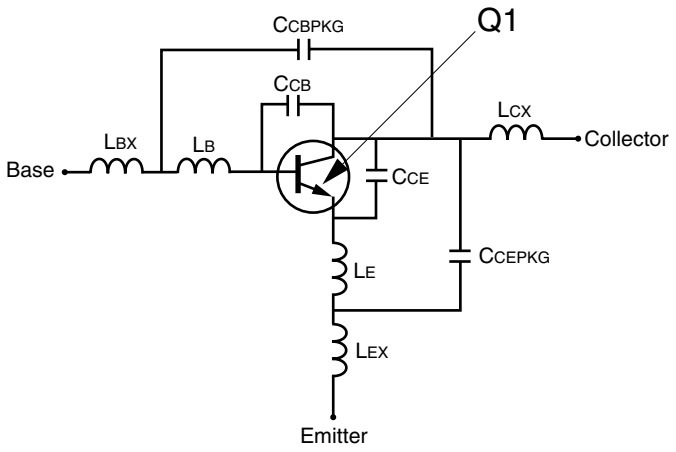
COLLECTOR CURRENT vs. COLLECTOR TO EMITTER VOLTAGE



FORWARD CURRENT GAIN vs. COLECTOR CURRENT



SCHEMATIC



BJT NONLINEAR MODEL PARAMETERS (1)

Parameters	Q1	Parameters	Q1
IS	239.6e-18	MJC	0.223
BF	125	XCJC	0
NF	0.9854	CJS	0
VAF	12	VJS	0.75
IKF	0.200	MJS	0
ISE	1.933e-6	FC	0.5
NE	50	TF	10e-12
BR	18.25	XTF	25
NR	0.9771	VTF	0.40
VAR	10	ITF	0.13
IKR	11.81e-3	PTF	43.1
ISC	1.55e-18	TR	0.3e-9
NC	1.860	EG	1.11
RE	0.870	XTB	0
RB	4.0	XTI	3
RBM	5.2	KF	0
IRB	1e-6	AF	1
RC	4.635		
CJE	1.2e-12		
VJE	0.77		
MJE	0.4844		
CJC	0.4e-12		
VJC	0.5275		

(1) Gummel-Poon Model

UNITS

Parameter	Units
time	seconds
capacitance	farads
inductance	henries
resistance	ohms
voltage	volts
current	amps

ADDITIONAL PARAMETERS

Parameters	681M03
CCB	0.07e-12
CCE	0.01e-12
LB	0.3e-9
LE	0.8e-9
CCBPKG	0.08e-12
CCEPKG	0.08e-12
LBX	0.12e-9
LCX	0.10e-9
LEX	0.12e-9

MODEL RANGE
Frequency: 0.1 to 5.0 GHz
Bias: V_{CE} = 2.5 V to 8 V, I_C = 0.3 mA to 20 mA
Date: 12/98
hFE = 124 at V_{CE} = 3 V, I_C = 7 mA

CEL California Eastern Laboratories

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Facsimile: (408) 988-0279

Subject: Compliance with EU Directives

CEL certifies, to its knowledge, that semiconductor and laser products detailed below are compliant with the requirements of European Union (EU) Directive 2002/95/EC Restriction on Use of Hazardous Substances in electrical and electronic equipment (RoHS) and the requirements of EU Directive 2003/11/EC Restriction on Penta and Octa BDE.

CEL Pb-free products have the same base part number with a suffix added. The suffix –A indicates that the device is Pb-free. The –AZ suffix is used to designate devices containing Pb which are exempted from the requirement of RoHS directive (*). In all cases the devices have Pb-free terminals. All devices with these suffixes meet the requirements of the RoHS directive.

This status is based on CEL's understanding of the EU Directives and knowledge of the materials that go into its products as of the date of disclosure of this information.

Restricted Substance per RoHS	Concentration Limit per RoHS (values are not yet fixed)	Concentration contained in CEL devices	
Lead (Pb)	< 1000 PPM	-A	-AZ
		Not Detected	(*)
Mercury	< 1000 PPM	Not Detected	
Cadmium	< 100 PPM	Not Detected	
Hexavalent Chromium	< 1000 PPM	Not Detected	
PBB	< 1000 PPM	Not Detected	
PBDE	< 1000 PPM	Not Detected	

If you should have any additional questions regarding our devices and compliance to environmental standards, please do not hesitate to contact your local representative.